ON Semiconductor

FINAL PRODUCT/PROCESS CHANGE NOTIFICATION #20041

Generic Copy

Issue Date: 28-Mar-2013

TITLE: Transfer Of High Voltage TMOS7 from ON Semiconductor fab located in Aizu, Japan to ON Semiconductor Fab in Roznov, Czech Republic.

PROPOSED FIRST SHIP DATE: 28-Jun-2013

AFFECTED CHANGE CATEGORY(S): Wafer Fabrication

FOR ANY QUESTIONS CONCERNING THIS NOTIFICATION:
Contact your local ON Semiconductor Sales Office or Mohd Hezri Abu Bakar <MohdHezri.AbuBakar@onsemi.com>

SAMPLES: Contact your local ON Semiconductor Sales Office or Brian Goodburn
< brian.goodburn@onsemi.com >

ADDITIONAL RELIABILITY DATA: Available
Contact your local ON Semiconductor Sales Office or Donna Scheuch <d.scheuch@onsemi.com >

NOTIFICATION TYPE:

Final Product/Process Change Notification (FPCN)

Final change notification sent to customers. FPCNs are issued at least 90 days prior to implementation of the change.

ON Semiconductor will consider this change approved unless specific conditions of acceptance are provided in writing within 30 days of receipt of this notice. To do so, contact <quality@onsemi.com>.

DESCRIPTION AND PURPOSE:

ON Semiconductor consolidated their manufacturing efforts by closing their Wafer facility in Aizu, Japan. This Aizu facility had been the source for High Cell Density (TMOS7) MOSFET Die. These MOSFET Die types are transferred, and will be sourced from the ON Semiconductor's Wafer facility in Roznov, Czech Republic.

Reliability Qualification and full electrical characterization over temperature have been performed.

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RELIABILITY DATA SUMMARY:

Reliability Test Results:

#	Test	Test Conditions	Read points	MMBF 170L	NTMD6601	NTD3055	NTD20P06L	NTB30N20	NTB30N15
1	AC-PC	Ta = 121°C/ 100% RH/ 15psig	96 hr	0/80	0/80	0/80	0/80	0/80	--
2	HAST-PC	130°C/85% RH Vds=80% or max rated or 100V maximum	96 hr	0/80	0/80	0/80	0/80	0/80	--
3	HTGB	TA = Max rated for 1008 hrs Vgs=100% of max rated	1008 hr	0/80	0/80	0/160	0/80	0/160	--
4	HTRB	TA = Max rated for 1008 hrs Vds=80% of max rated	1008 hr	0/80	0/80	0/160	0/80	0/80	0/240
5	IOL-PC	Ta=25'C, delta Tj=100'C, 2-min on/off, 15K- cy	15000 cyc	0/80	0/80	0/80	0/80	0/80	--
6	TC-PC	-55°C to +150°C	1000 hr	0/80	0/80	0/80	0/80	0/80	--

ELECTRICAL CHARACTERISTIC SUMMARY:

There is no change in electrical parametric performance. Characterization data is available upon request.

CHANGED PART IDENTIFICATION:

There will be no physical change to the Devices assembled with ON Semiconductor Die from Roznov, CR. There will be Wafer Lot traceability from the manufacturing Lot to determine the Die origin. Product assembled with the Die fabricated from the Roznov wafer facility will have a Finish Good Date Code no earlier than Work Week 25, 2013.

List of affected General Parts:

BSS123LT1G
BVSS123LT1G
NTB35N15T4G
SMBF1035LT3G